Unit: mm

TOSHIBA Field Effect Transistor Silicon N Channel Junction Type

# 2SK711

High Frequency Amplifier Applications
AM High Frequency Amplifier Applications
Audio Frequency Amplifier Applications

• High  $|Y_{fs}|$ :  $|Y_{fs}| = 25 \text{ mS (typ.)}$ 

• Low  $C_{iss}$ :  $C_{iss} = 7.5 pF$  (typ.)

#### **Maximum Ratings (Ta = 25°C)**

Characteristics	Symbol	Rating	Unit	
Gate-drain voltage	$V_{GDS}$	-20	٧	
Gate current	IG	10	mA	
Drain power dissipation	P <sub>D</sub>	150	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T <sub>stg</sub>	-55~125	°C	

	Offic. Hilli
1. SOURC 2. DRAIN 3. GATE	2.5-0.3 +0.25 1.5-0.15 1.000 +0.0
JEDEC	TO-236MOD
JEITA	SC-59
TOSHIBA	2-3F1B

Weight: 0.012 g (typ.)

### **Electrical Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = -15 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	-1.0	nA
Gate-drain breakdown voltage	V (BR) GDS	$V_{DS}=0~V,~I_G=-100~\mu A$	-20	_	_	V
Drain current	I <sub>DSS</sub> (Note)	V <sub>DS</sub> = 5 V, V <sub>GS</sub> = 0 V	6	_	32	mA
Gate-source cut-off voltage	V <sub>GS</sub> (OFF)	$V_{DS} = 5 \text{ V}, I_{D} = 1 \mu A$	_	_	-2.5	V
Forward transfer admittance	Y <sub>fs</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ kHz}$	15	25	_	mS
Input capacitance	C <sub>iss</sub>	$V_{DS} = 5 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	7.5	10	pF
Reverse transfer capacitance	C <sub>rss</sub>	$V_{DS} = 5 \text{ V}, I_D = 0 \text{ mA}, f = 1 \text{ MHz}$	_	2	3	pF

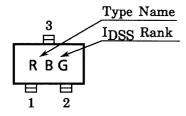
Note: IDSS classification

GR: 6~12 mA, BL: 10~20 mA, V: 16~32 mA

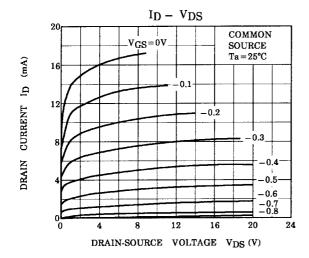
G) (L) (V)

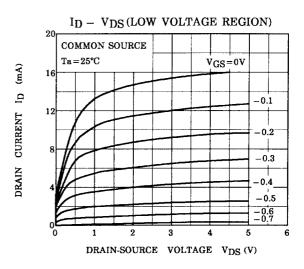
( ).....I<sub>DSS</sub> rank marking

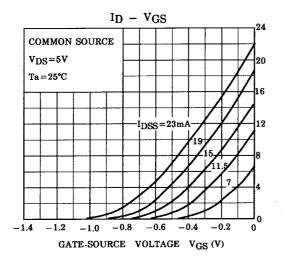
## Marking

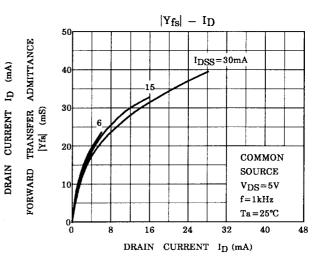


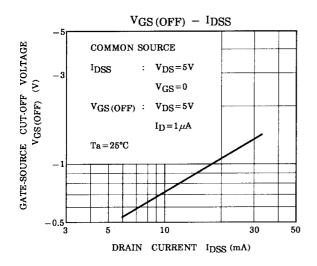
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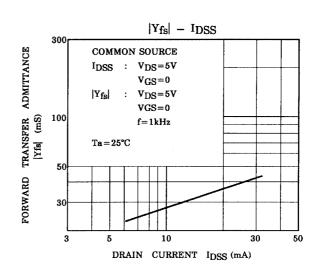


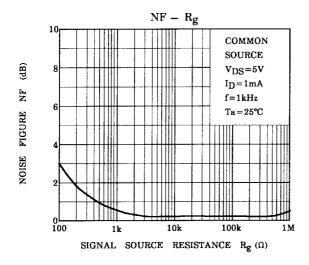


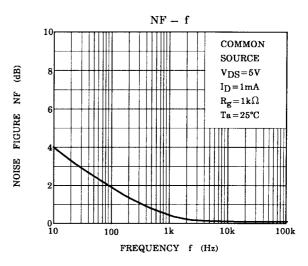


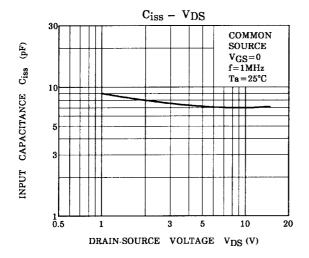


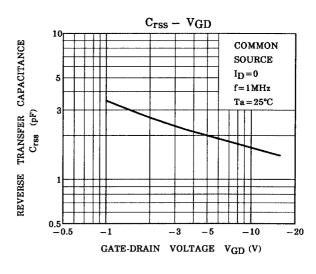


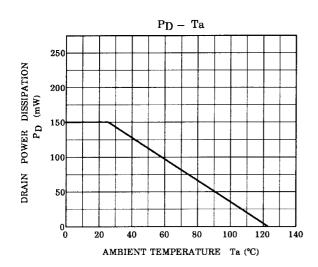












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